

具有可控开启功能的超小型低导通电阻负载开关

查询样品: [TPS22913](#)

特性

- 集成单负载开关
- 超小型 **0.9mm × 0.9mm, 0.5mm** 螺距 **CSP-4** 封装
- 输入电压范围: **1.4-V** 至 **5.5-V**
- 低导通电阻
 - 在 **V_{IN} = 5-V**时, **r_{ON} = 60-mΩ**
 - 在 **V_{IN} = 3.3-V**时, **r_{ON} = 61-mΩ**
 - 在 **V_{IN} = 1.8-V**时, **r_{ON} = 74-mΩ**
 - 在 **V_{IN} = 1.5-V**时, **r_{ON} = 84-mΩ**
- **2-A** 最大持续开关电流
- 低阈值控制输入
- 可控的转换率选项
- 欠压闭锁
- 快速输出放电晶体管
- 反向电流保护

应用范围

- 便携式工业用设备
- 便携式医疗设备
- 便携式媒体播放器
- 销售点终端机
- **GPS**设备
- 数码摄像机
- 便携式仪器
- 智能电话

说明

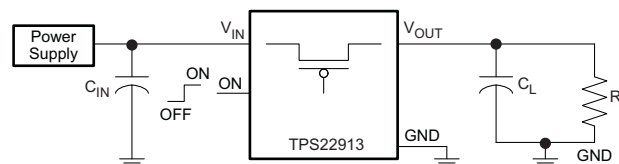
TPS22913 是一款具有可控开启功能的小型低 r_{ON} 负载的开关。此器件包含一个 P-通道 MOSFET，此 MOSFET 可在输入电压 1.4 V 至 5.5 V 区间内工作。此开关由一个开/关输入 (ON) 控制并能与低电压控制信号直接连接。TPS22913 高电平有效。

TPS22913 包含一个 150-Ω 片载电阻器，此电阻器用于当开关关闭时的快速输出放电。为了避免突入电流，此器件的上升时间由内部控制。TPS22913 系列产品具有不同的转换速率选项 (参看 Table 1)。

在反向电压的情况下，通过锁住电源开关，TPS22913 提供电路断路器功能。当输出电压被驱动至高于输入电压 (V_{IN}) 以快速 (10μs 典型值) 停止电流流向开关的输入端时，一个内部反向电压比较器使电源开关失效。当电源开关处于开启 (ON) 状态时，反向电流保护功能被激活。除此之外，在欠压闭锁期间，或者在开关关闭期间，由于开关内的二极管没有工作，所以没有反向电流产生。

TPS22913 采用超小型，节约空间的 4-引脚 C 无效 SP 封装，其在自然环境中的额定工作温度范围为 -40°C 至 85°C。

典型应用



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Table 1. Feature List

DEVICE	r_{ON} (typ) at 3.3 V	SLEW RATE (typ)	QUICK OUTPUT DISCHARGE ⁽¹⁾	MAXIMUM OUTPUT CURRENT	ENABLE
TPS22913A ⁽²⁾	63 mΩ	0.1 μs/V	Yes	2-A	Active High
TPS22913B	63 mΩ	20 μs/V	Yes	2-A	Active High
TPS22913C	63 mΩ	200 μs/V	Yes	2-A	Active High
TPS22913D ⁽²⁾	63 mΩ	900 μs/V	Yes	2-A	Active High

(1) This feature discharges the output of the switch to ground through an 150-Ω resistor, preventing the output from floating.

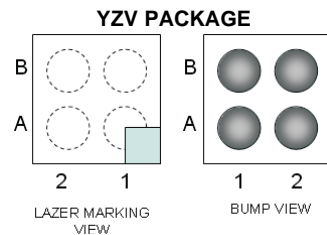
(2) Contact local sales/distributor or factory for availability.

ORDERING INFORMATION

T _A	PACKAGE ⁽¹⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING/ STATUS ⁽²⁾
-40°C to 85°C	YZV (0.5mm pitch)	Tape and Reel	TPS22913AYZVR	Contact factory for availability
-40°C to 85°C	YZV (0.5mm pitch)	Tape and Reel	TPS22913BYZVR	---- 64
-40°C to 85°C	YZV (0.5mm pitch)	Tape and Reel	TPS22913CZVR	---- 76
-40°C to 85°C	YZV (0.5mm pitch)	Tape and Reel	TPS22913DYZVR	Contact factory for availability

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

(2) Contact factory for details and availability for PREVIEW devices, minimum order quantities may apply.

DEVICE INFORMATION

TERMINALS ASSIGNMENTS

B	ON	GND
A	V _{IN}	V _{OUT}
	2	1

PIN FUNCTIONS

TPS22913	PIN NAME	DESCRIPTION
YZV		
B1	GND	Ground
B2	ON	Switch control input, active high. Do not leave floating
A1	V _{OUT}	Switch output
A2	V _{IN}	Switch input, bypass this input with a ceramic capacitor to ground

BLOCK DIAGRAM

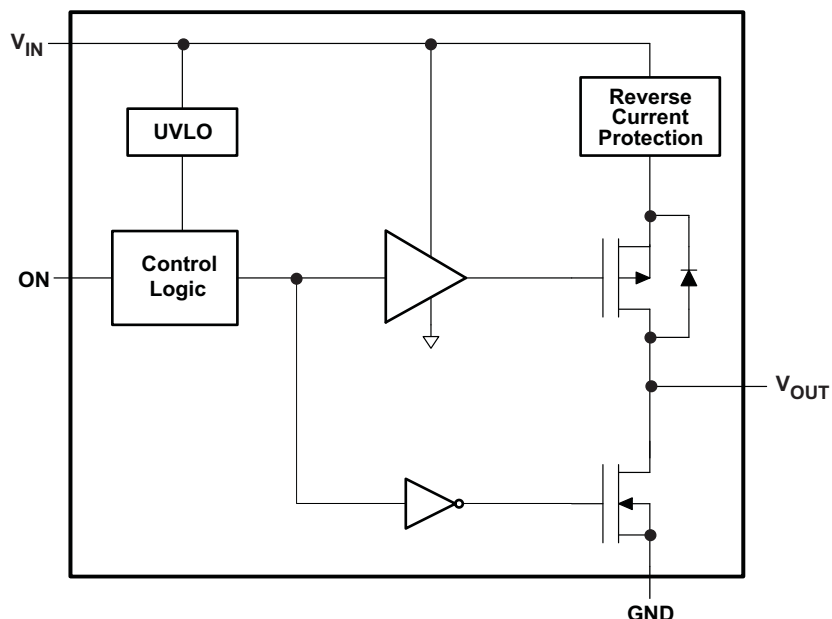


Table 2. FUNCTION TABLE

ON	VIN to VOUT	VOUT to GND ⁽¹⁾
L	OFF	ON
H	ON	OFF

(1) See Application section 'Output Pull-Down'

ABSOLUTE MAXIMUM RATINGS

		VALUE	UNIT
V _{IN}	Input voltage range	-0.3 to 6	V
V _{OUT}	Output voltage range	V _{IN} + 0.3	V
V _{ON}	Input voltage range	-0.3 to 6	V
I _{MAX}	Maximum continuous switch current	2	A
I _{PLS}	Maximum pulsed switch current, pulse <300 μS, 2% duty cycle	2.5	A
T _A	Operating free-air temperature range	-40 to 85	°C
T _J	Maximum junction temperature	125	°C
T _{STG}	Storage temperature range	-65 to 150	°C
T _{LEAD}	Maximum lead temperature (10-s soldering time)	300	°C
ESD	Electrostatic discharge protection	Human-Body Model (HBM) (V _{IN} , V _{OUT} , GND pins)	2000
		Charged-Device Model (CDM) (V _{IN} , V _{OUT} , ON, GND pins)	1000

THERMAL INFORMATION

THERMAL METRIC ⁽¹⁾		TPS22913		UNITS
		CSP		
		(4) PINS		
θ_{JA}	Junction-to-ambient thermal resistance	189.1		°C/W
θ_{JCTop}	Junction-to-case (top) thermal resistance	1.9		
θ_{JB}	Junction-to-board thermal resistance	36.8		
ψ_{JT}	Junction-to-top characterization parameter	11.3		
ψ_{JB}	Junction-to-board characterization parameter	36.8		
θ_{JCbot}	Junction-to-case (bottom) thermal resistance	N/A		

(1) 有关传统和新的热度的更多信息，请参阅 IC 封装热量量 应用报告 [SPRA953](#)。

RECOMMENDED OPERATING CONDITIONS

			MIN	MAX	UNIT
V_{IN}	Input voltage range		1.4	5.5	V
V_{ON}	ON voltage range		0	5.5	V
V_{OUT}	Output voltage range			V_{IN}	
V_{IH}	High-level input voltage, ON	$V_{IN} = 3.61\text{ V to }5.5\text{ V}$	1.1	5.5	V
		$V_{IN} = 1.4\text{ V to }3.6\text{ V}$	1.1	5.5	V
V_{IL}	Low-level input voltage, ON	$V_{IN} = 3.61\text{ V to }5.5\text{ V}$		0.6	V
		$V_{IN} = 1.4\text{ V to }3.6\text{ V}$		0.4	V
C_{IN}	Input Capacitor		1 ⁽¹⁾		μF

(1) Refer to the application section.

ELECTRICAL CHARACTERISTICS

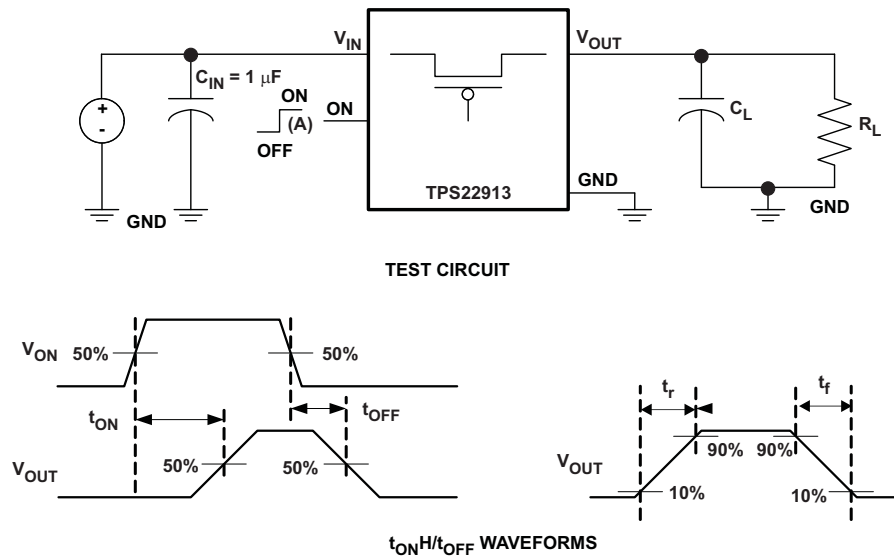
VIN = 1.4 V to 5.5 V, TA = –40°C to 85°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TA	MIN	TYP	MAX	UNIT
IIN	Quiescent current	IOUT = 0, VIN = VON = 5.25 V	Full		2	10	µA
		IOUT = 0, VIN = VON = 4.2 V			2	7.0	
		IOUT = 0, VIN = VON = 3.6 V			2	7.0	
		IOUT = 0, VIN = VON = 2.5 V			0.9	5	
		IOUT = 0, VIN = VON = 1.5 V			0.7	5	
IIN(off)	Off supply current	VON = GND, VOUT = Open, VIN = 5.25 V	Full		1.2	10	µA
		VON = GND, VOUT = Open, VIN = 4.2 V			0.2	7.0	
		VON = GND, VOUT = Open, VIN = 3.6 V			0.1	7.0	
		VON = GND, VOUT = Open, VIN = 2.5 V			0.1	5	
		VON = GND, VOUT = Open, VIN = 1.5 V			0.1	5	
IIN(Leakage)	Leakage current	VON = GND, VOUT = 0, VIN = 5.25 V	Full		1.2	10	µA
		VON = GND, VOUT = 0, VIN = 4.2 V			0.2	7.0	
		VON = GND, VOUT = 0, VIN = 3.6 V			0.1	7.0	
		VON = GND, VOUT = 0, VIN = 2.5 V			0.1	5	
		VON = GND, VOUT = 0, VIN = 1.5 V			0.1	5	
rON	On-resistance	VIN = 5.25 V, IOUT = –200 mA	25°C		60	80	mΩ
			Full			110	
		VIN = 5.0 V, IOUT = –200 mA	25°C		60	80	
			Full			110	
		VIN = 4.2 V, IOUT = –200 mA	25°C		60	80	
			Full			110	
		VIN = 3.3 V, IOUT = –200 mA	25°C		60.7	80	
			Full			110	
		VIN = 2.5 V, IOUT = –200 mA	25°C		63.4	90	
			Full			120	
		VIN = 1.8 V, IOUT = –200 mA	25°C		74.2	100	
			Full			130	
		VIN = 1.5 V, IOUT = –200 mA	25°C		83.9	120	
			Full			150	
RPD	Output pull down resistance	VIN = 3.3 V, VON = 0, IOUT = 30 mA	25°C		153	200	Ω
UVLO	Under voltage lockout	VIN increasing, VON = 3.6 V, IOUT = –100 mA	Full			1.2	V
				VIN decreasing, VON 3.6 V, RL = 10 Ω		0.50	
ION	ON input leakage current	VON = 1.4 V to 5.25 V or GND	Full			1	µA
VRVP	Reverse Current Voltage Threshold				44		mV
tDELAY	Reverse Current Response Delay	VIN = 5V			10		µs

SWITCHING CHARACTERISTICS

PARAMETER	TEST CONDITION	TPS22913 B	TPS22913 C	UNIT
		TYP	TYP	
VIN = 5 V, TA = 25°C (unless otherwise noted)				
t _{ON} Turn-ON time	R _L = 10 Ω, C _L = 0.1 μF	76	770	μs
t _{OFF} Turn-OFF time	R _L = 10 Ω, C _L = 0.1 μF	6.6	6.6	
t _R VOUT rise time	R _L = 10 Ω, C _L = 0.1 μF	82	838	
t _F VOUT fall time	R _L = 10 Ω, C _L = 0.1 μF	3	3	
VIN = 3.3 V, TA = 25°C (unless otherwise noted)				
t _{ON} Turn-ON time	R _L = 10 Ω, C _L = 0.1 μF	102	1048	μs
t _{OFF} Turn-OFF time	R _L = 10 Ω, C _L = 0.1 μF	8.5	8.6	
t _R VOUT rise time	R _L = 10 Ω, C _L = 0.1 μF	97	980	
t _F VOUT fall time	R _L = 10 Ω, C _L = 0.1 μF	3	3	
VIN = 1.5 V, TA = 25°C (unless otherwise noted)				
t _{ON} Turn-ON time	R _L = 10 Ω, C _L = 0.1 μF	234	2344	μs
t _{OFF} Turn-OFF time	R _L = 10 Ω, C _L = 0.1 μF	17	18	
t _R VOUT rise time	R _L = 10 Ω, C _L = 0.1 μF	244	1823	
t _F VOUT fall time	R _L = 10 Ω, C _L = 0.1 μF	6.5	6.5	

PARAMETRIC MEASUREMENT INFORMATION



(A) Rise and fall times of the control signal is 100 ns.

A. Rise and fall times of the control signal is 100 ns.

Figure 1. Test Circuit and t_{ON}/t_{OFF} Waveforms

TYPICAL CHARACTERISTICS

ON-STATE RESISTANCE
vs
INPUT VOLTAGE

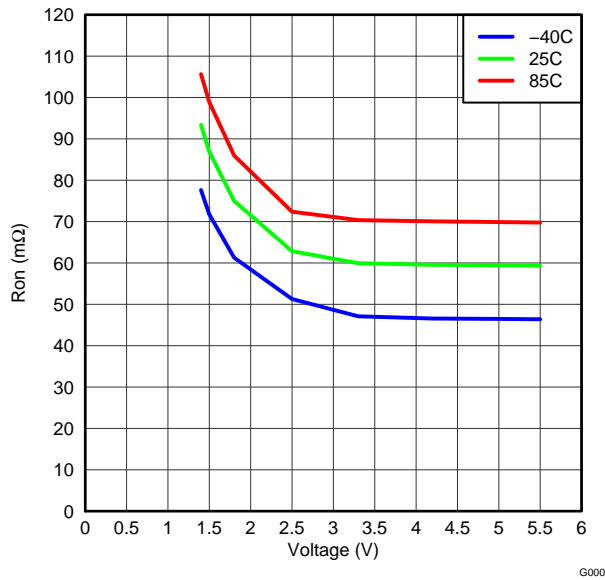


Figure 2.

ON INPUT THRESHOLD

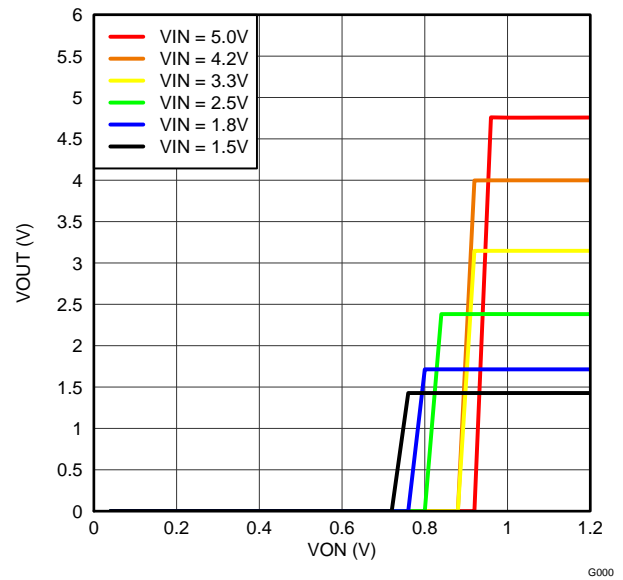


Figure 3.

INPUT CURRENT, QUIESCENT
vs
INPUT VOLTAGE

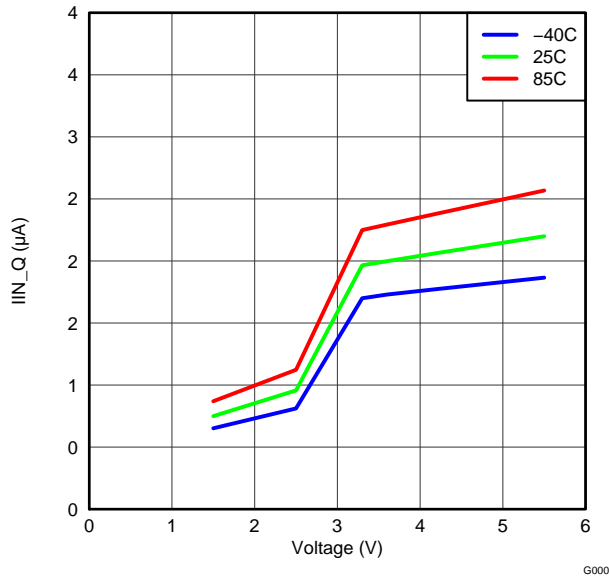


Figure 4.

INPUT CURRENT, LEAK
vs
INPUT VOLTAGE

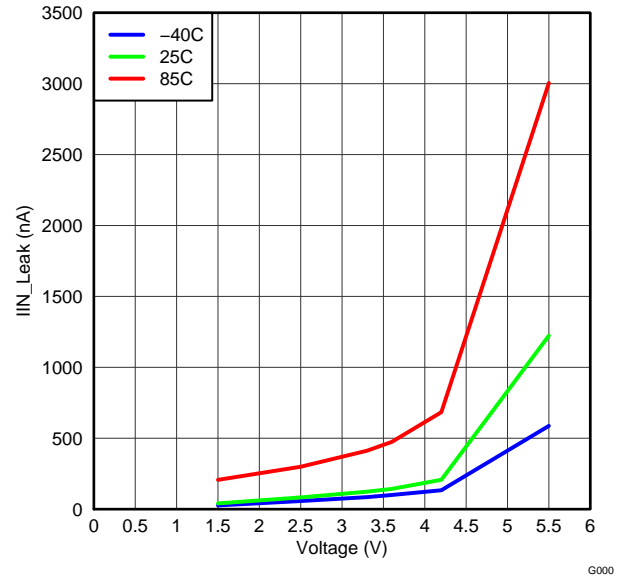


Figure 5.

TYPICAL CHARACTERISTICS (continued)

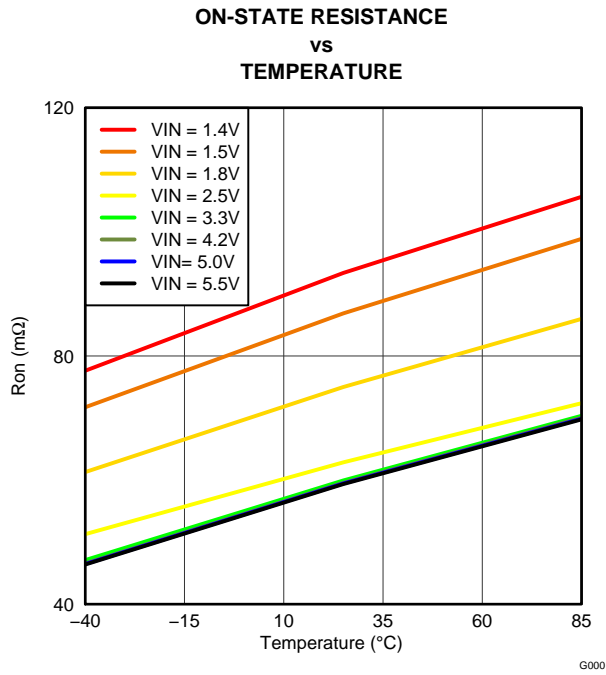


Figure 6.

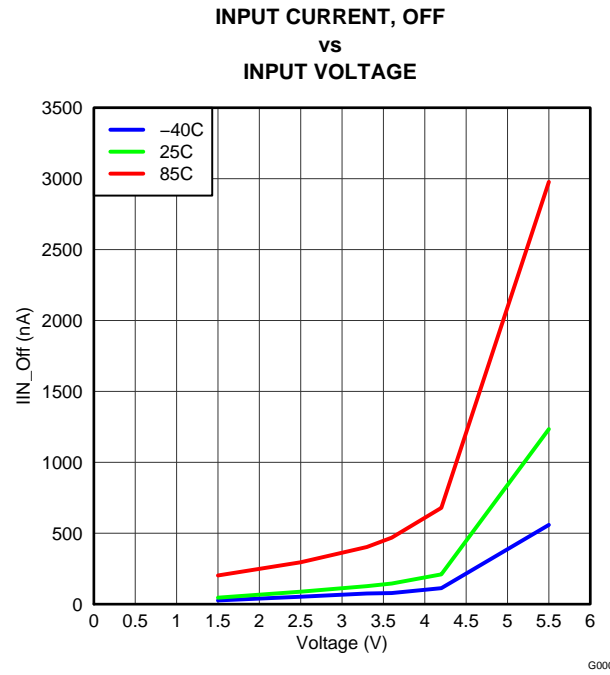


Figure 7.

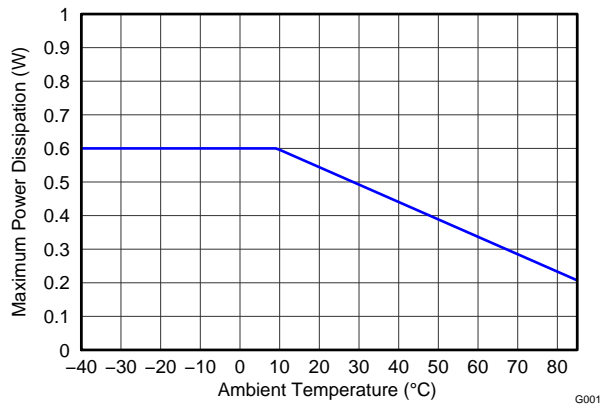


Figure 8. Allowable Power Dissipation

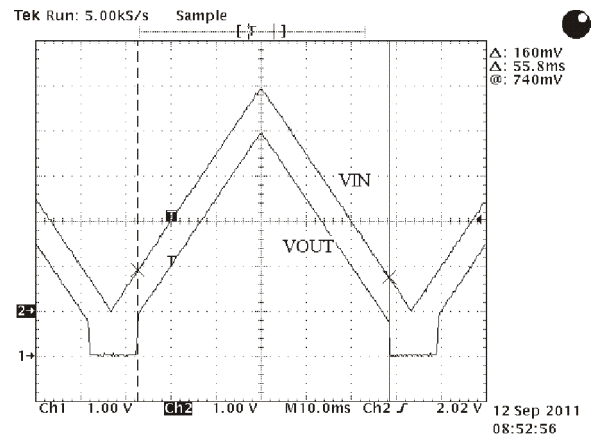


Figure 9. ULVO Response I_{OUT} = -100mA

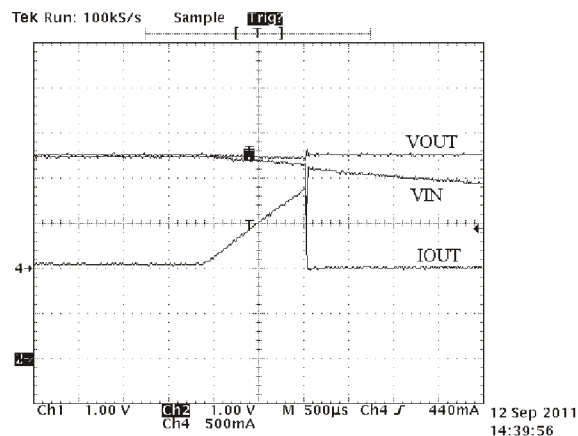


Figure 10. Reverse Current Protection V_{OUT} = 3.3V, V_{IN} = 3.3V Decreasing to 0V

TYPICAL CHARACTERISTICS (continued)
TYPICAL AC CHARACTERISTICS FOR TPS22913B

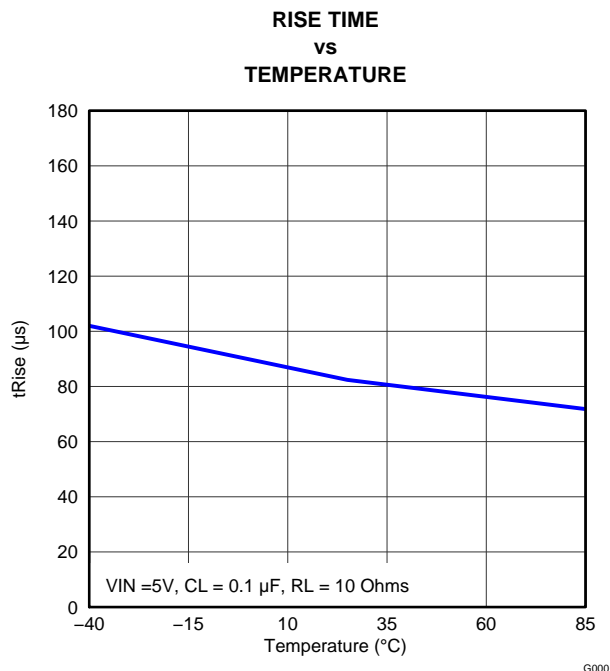


Figure 11.

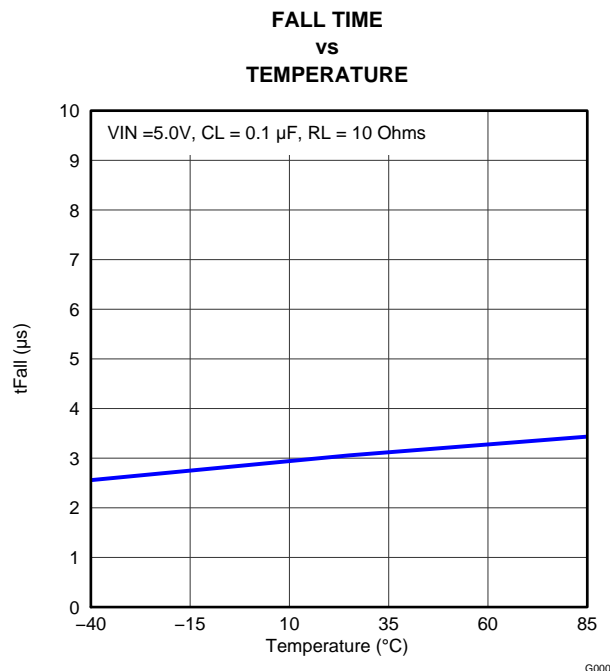


Figure 12.

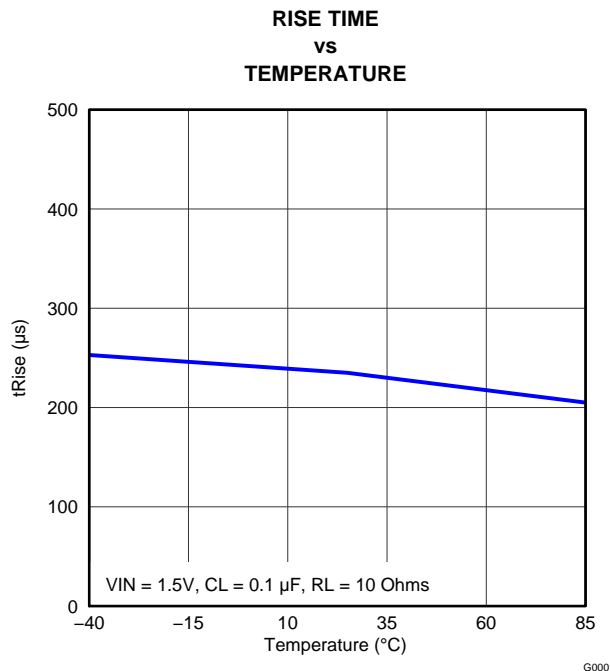


Figure 13.

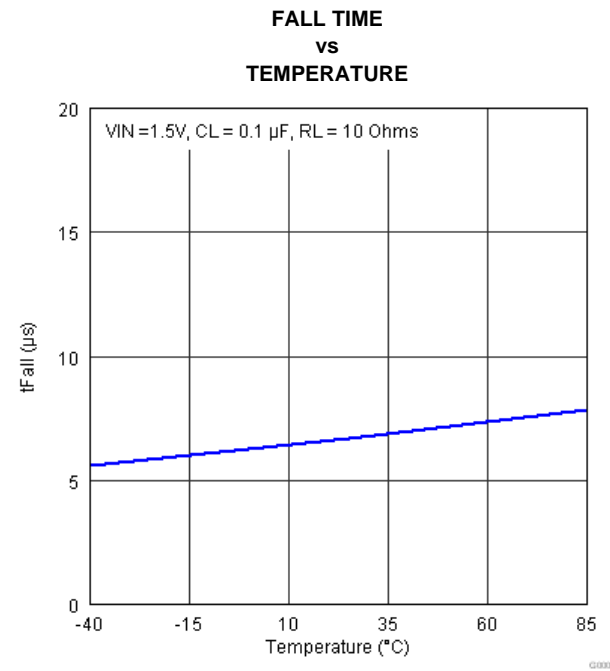


Figure 14.

TYPICAL CHARACTERISTICS (continued)

TURN-ON TIME
vs
TEMPERATURE

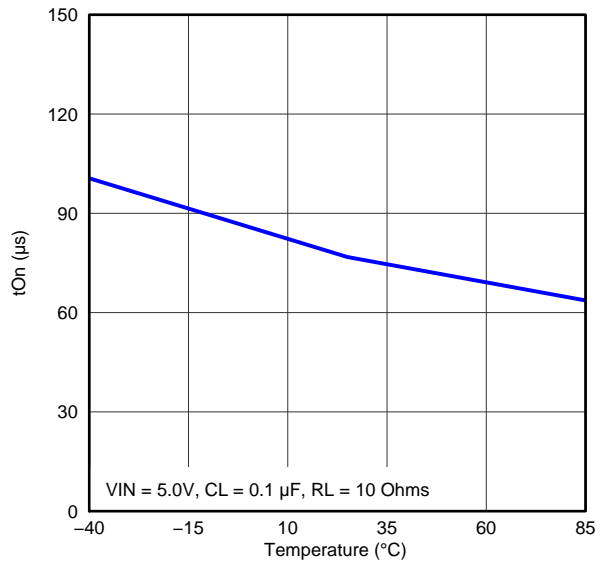


Figure 15.

TURN-OFF TIME
vs
TEMPERATURE

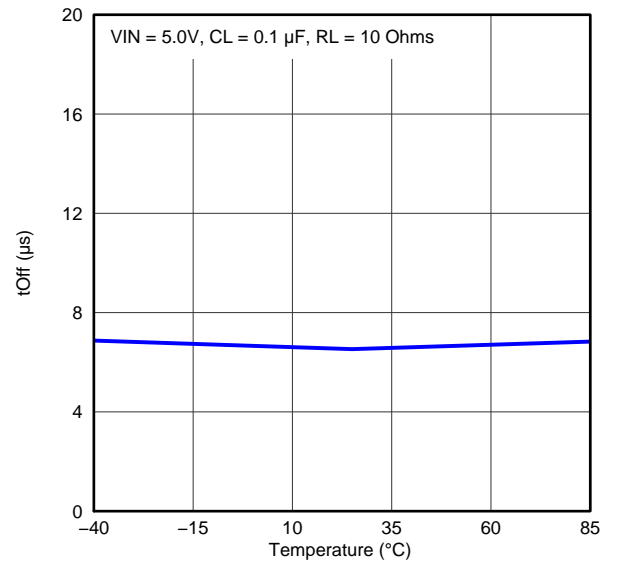


Figure 16.

TURN-ON TIME
vs
TEMPERATURE

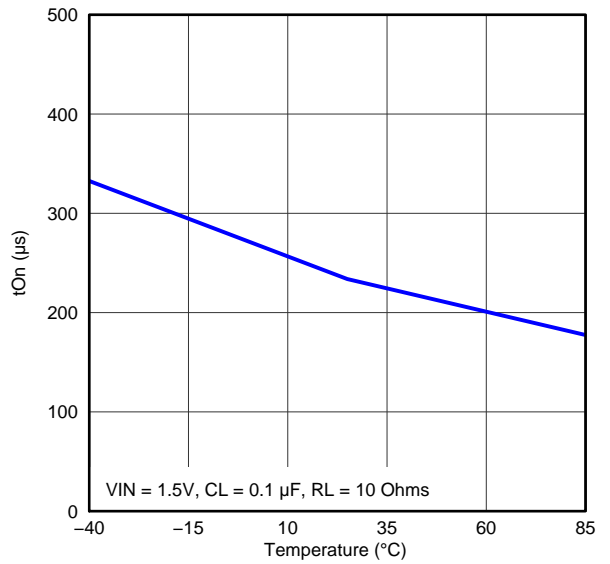


Figure 17.

TURN-OFF TIME
vs
TEMPERATURE

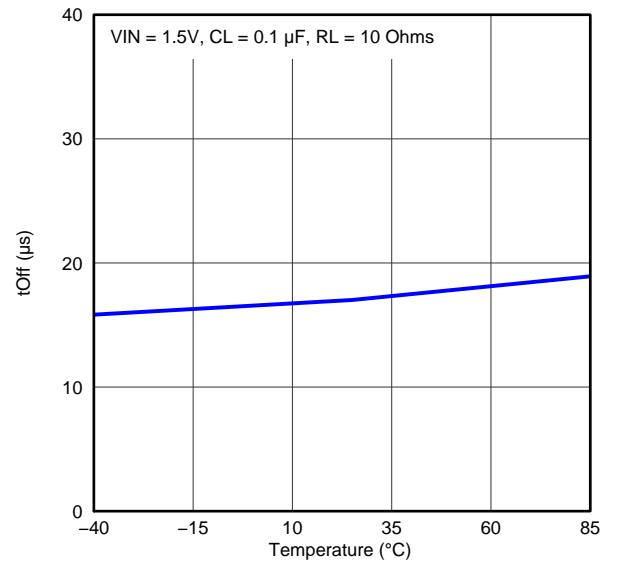


Figure 18.

TYPICAL CHARACTERISTICS (continued)

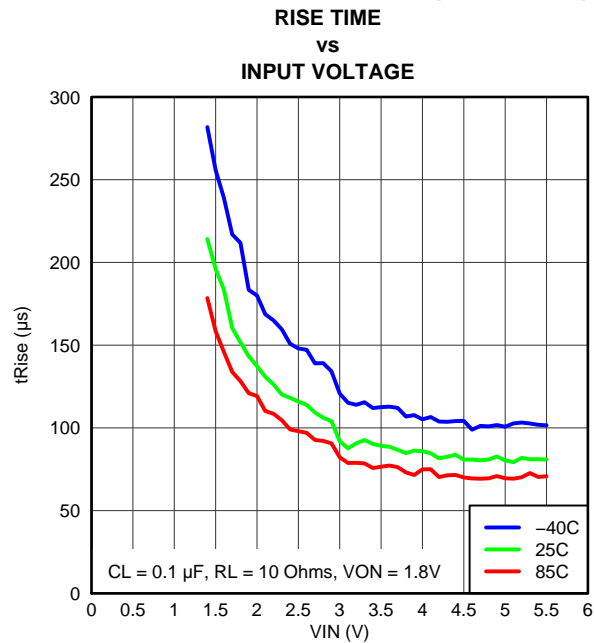


Figure 19.

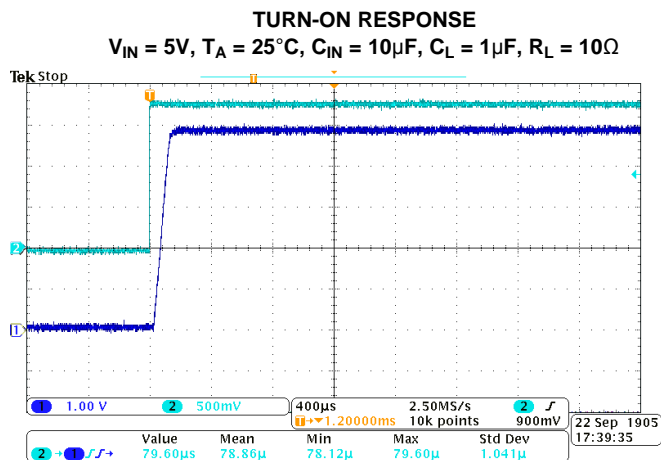


Figure 20.

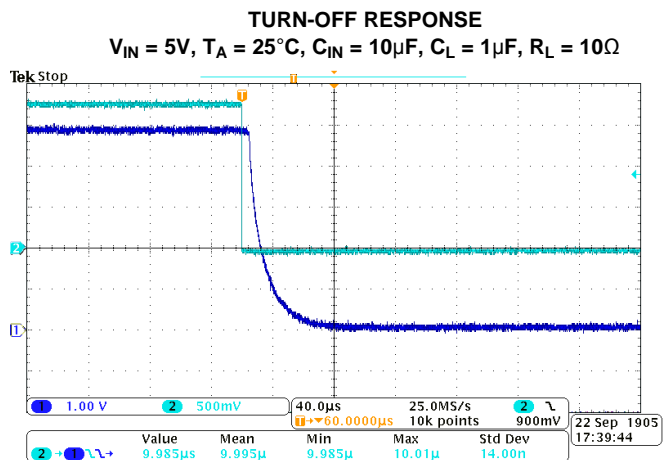


Figure 21.

TYPICAL CHARACTERISTICS (continued)

TURN-ON RESPONSE TIME

$V_{IN} = 5V, T_A = 25^\circ C, C_{IN} = 1\mu F, C_L = 0.1\mu F, R_L = 10\Omega$

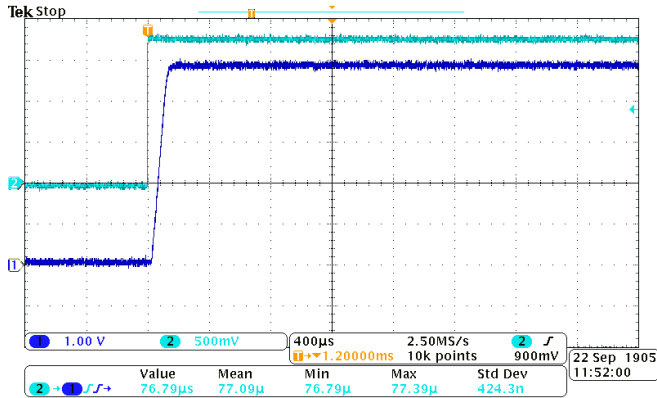


Figure 22.

TURN-OFF RESPONSE TIME

$V_{IN} = 5V, T_A = 25^\circ C, C_{IN} = 1\mu F, C_L = 0.1\mu F, R_L = 10\Omega$

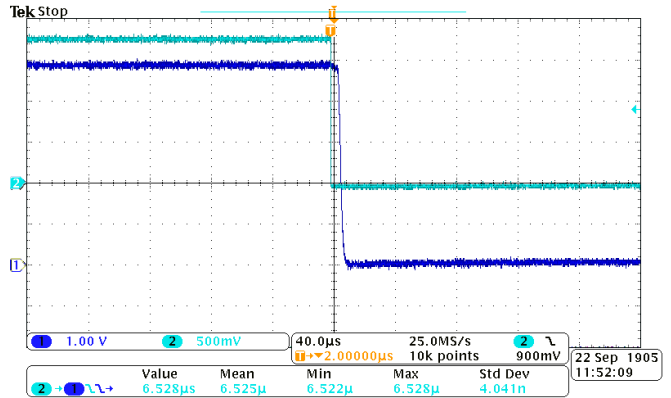


Figure 23.

TURN-Of RESPONSE TIME

$V_{IN} = 1.5V, T_A = 25^\circ C, C_{IN} = 10\mu F, C_L = 1\mu F, R_L = 10\Omega$

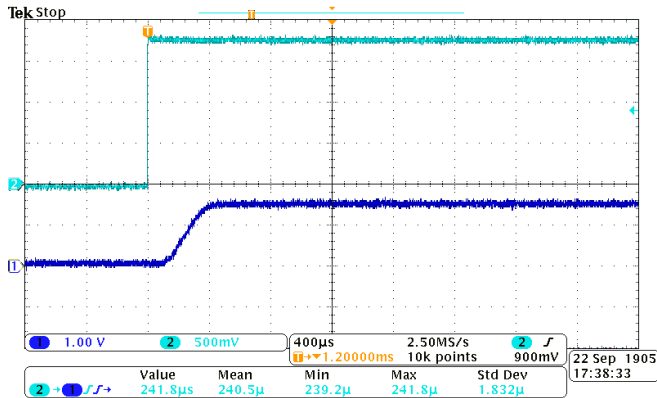


Figure 24.

TURN-Of RESPONSE TIME

$V_{IN} = 1.5V, T_A = 25^\circ C, C_{IN} = 10\mu F, C_L = 1\mu F, R_L = 10\Omega$

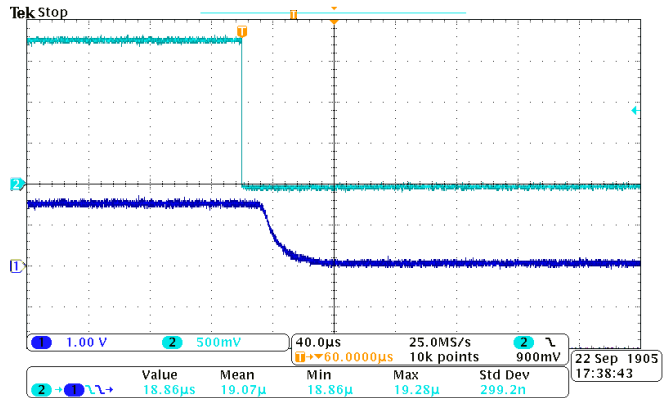


Figure 25.

TURN-Of RESPONSE TIME

$V_{IN} = 1.5V, T_A = 25^\circ C, C_{IN} = 1\mu F, C_L = 0.1\mu F, R_L = 10\Omega$

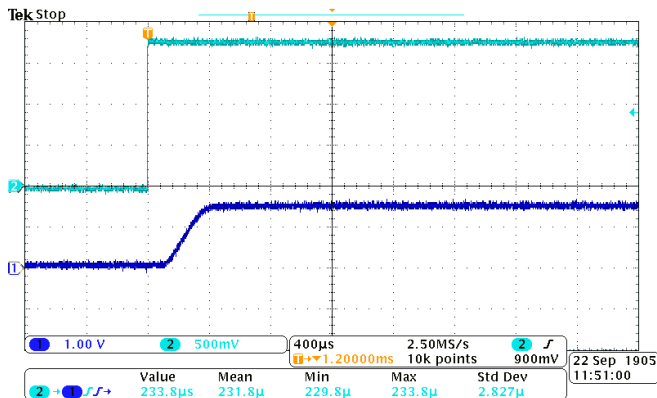


Figure 26.

TURN-Of RESPONSE TIME

$V_{IN} = 1.5V, T_A = 25^\circ C, C_{IN} = 1\mu F, C_L = 0.1\mu F, R_L = 10\Omega$

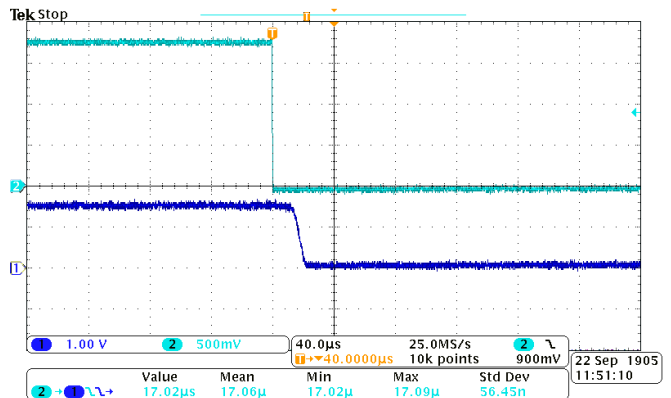


Figure 27.

TYPICAL CHARACTERISTICS (continued)
TYPICAL AC CHARACTERISTICS FOR TPS22913C

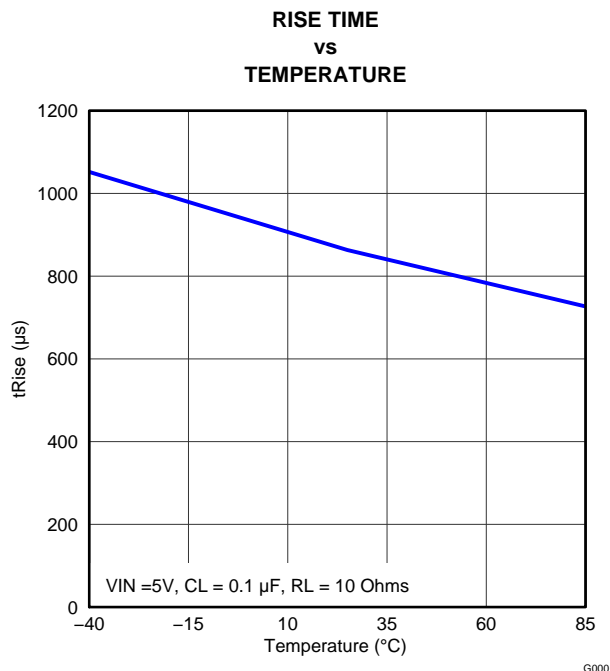


Figure 28.

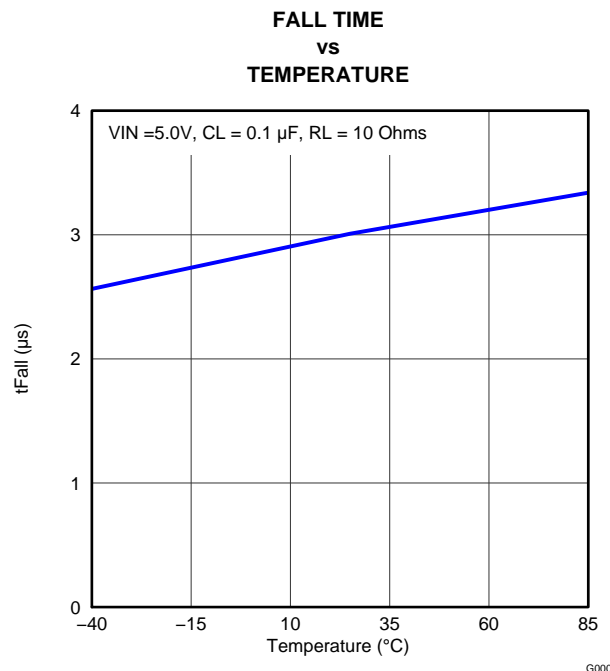


Figure 29.

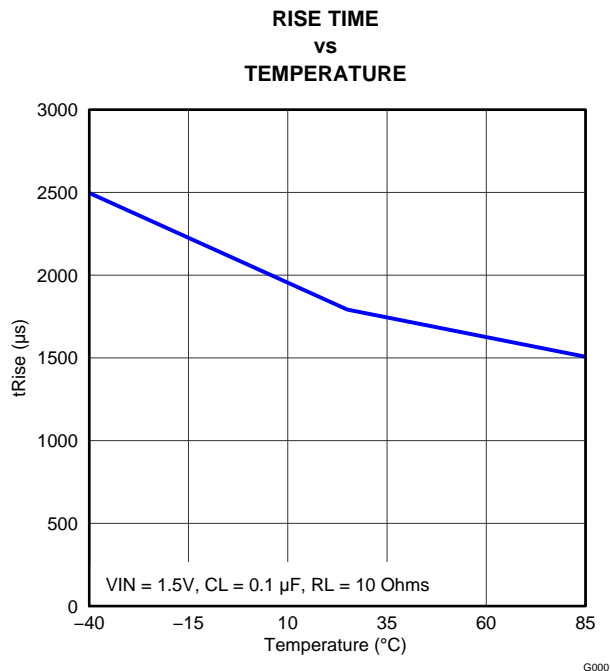


Figure 30.

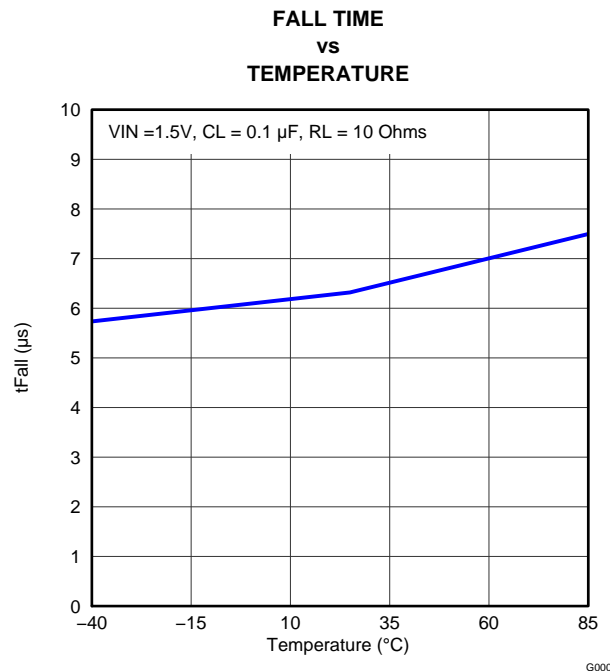


Figure 31.

TYPICAL CHARACTERISTICS (continued)

TURN-ON TIME
vs
TEMPERATURE

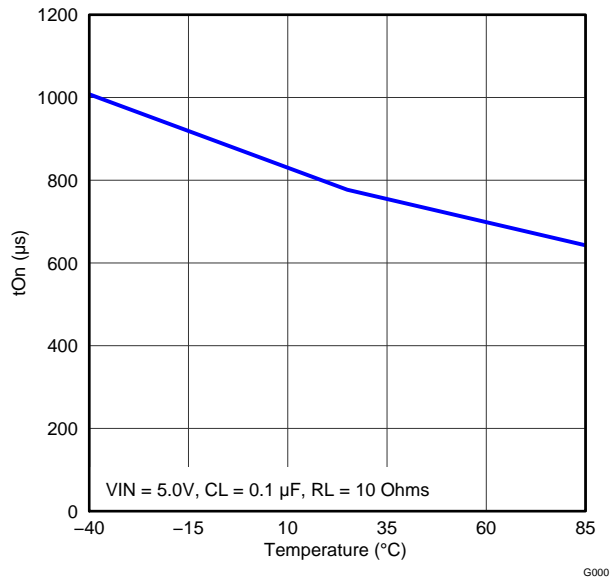


Figure 32.

TURN-OFF TIME
vs
TEMPERATURE

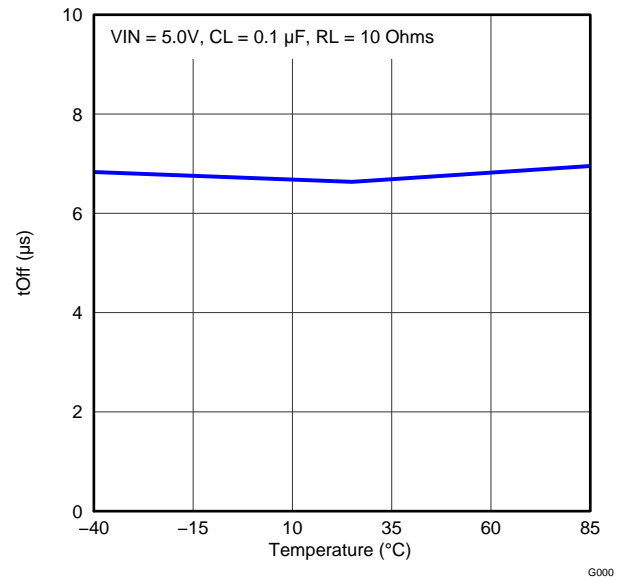


Figure 33.

TURN-ON TIME
vs
TEMPERATURE

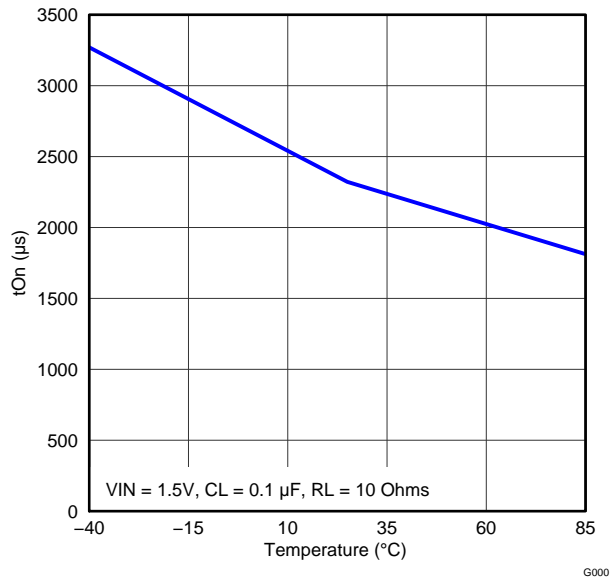


Figure 34.

TURN-OFF TIME
vs
TEMPERATURE

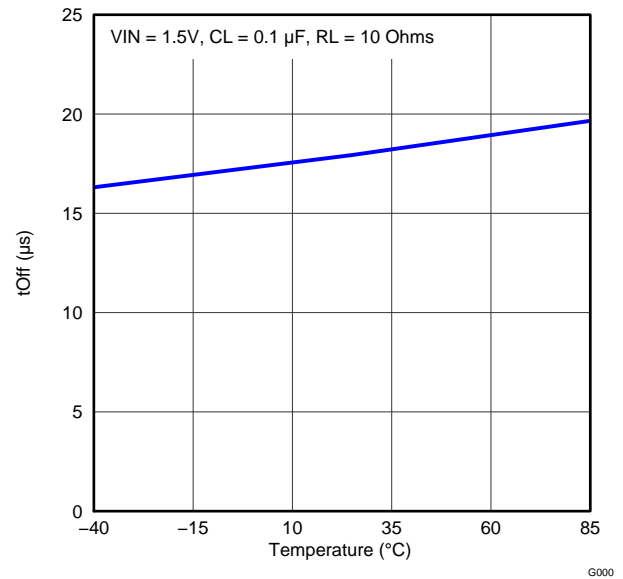


Figure 35.

TYPICAL CHARACTERISTICS (continued)

RISE TIME
vs
INPUT VOLTAGE

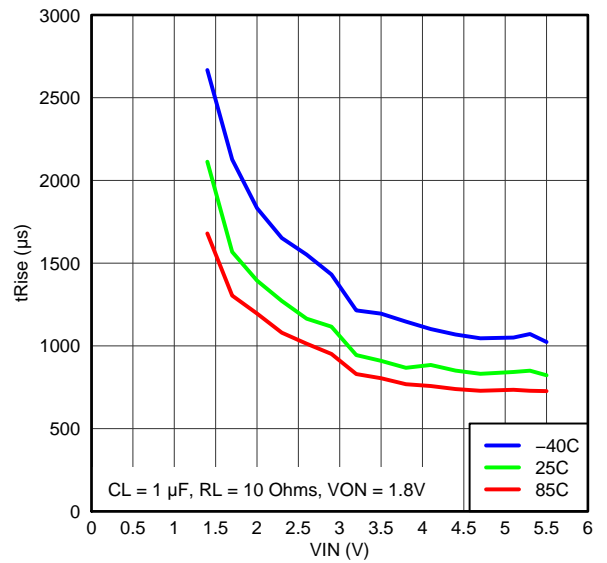


Figure 36.

TURN-ON RESPONSE

V_{IN} = 5V, T_A = 25°C, C_{IN} = 10µF, C_L = 1µF, R_L = 10Ω

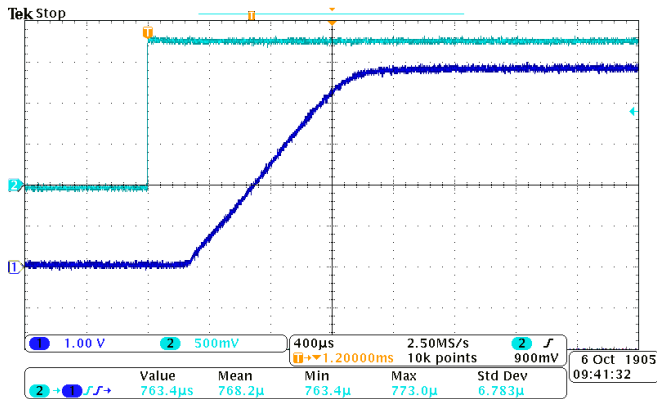


Figure 37.

TURN-OFF RESPONSE

V_{IN} = 5V, T_A = 25°C, C_{IN} = 10µF, C_L = 1µF, R_L = 10Ω

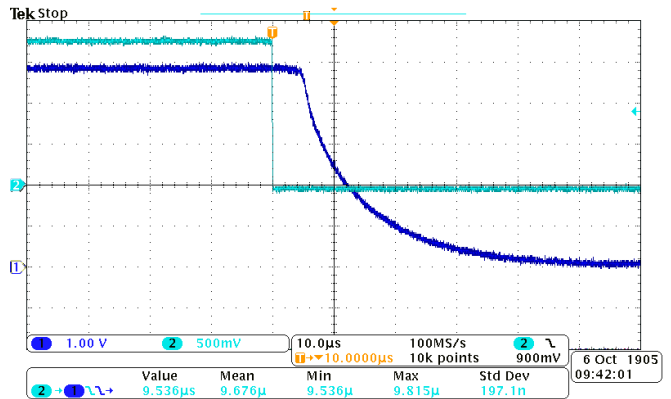


Figure 38.

TYPICAL CHARACTERISTICS (continued)

TURN-ON RESPONSE TIME

$V_{IN} = 5V, T_A = 25^\circ C, C_{IN} = 1\mu F, C_L = 0.1\mu F, R_L = 10\Omega$

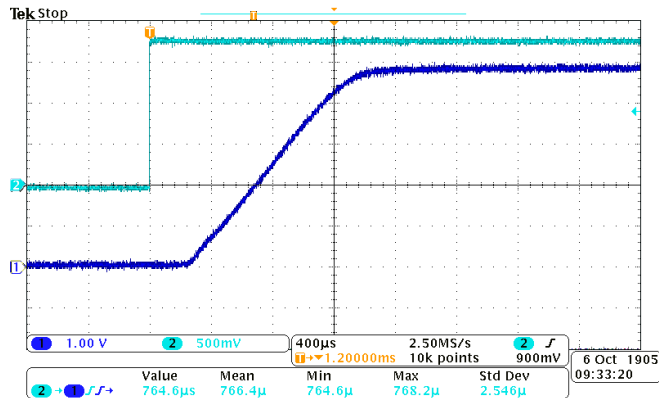


Figure 39.

TURN-OFF RESPONSE TIME

$V_{IN} = 5V, T_A = 25^\circ C, C_{IN} = 1\mu F, C_L = 0.1\mu F, R_L = 10\Omega$

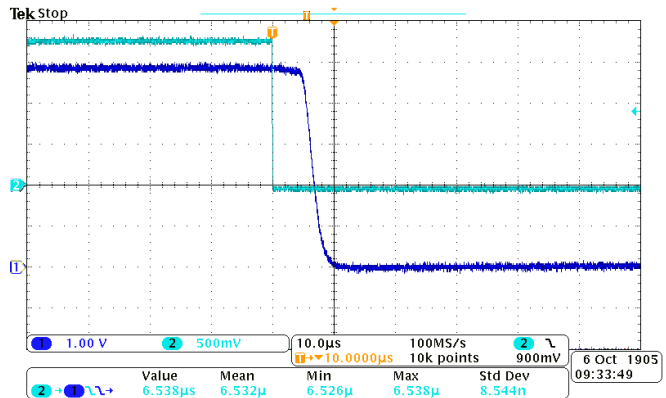


Figure 40.

TURN-Of RESPONSE TIME

$V_{IN} = 1.5V, T_A = 25^\circ C, C_{IN} = 10\mu F, C_L = 1\mu F, R_L = 10\Omega$

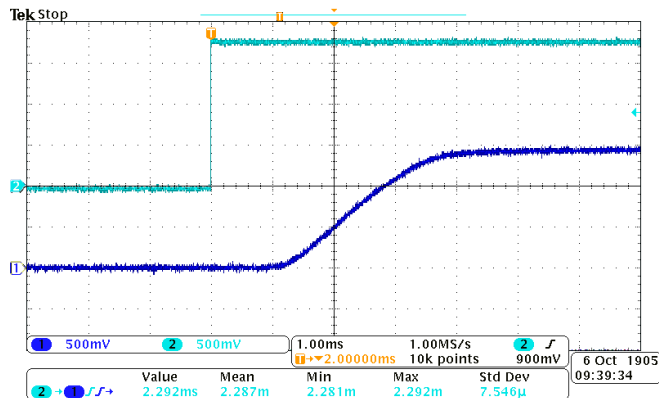


Figure 41.

TURN-Of RESPONSE TIME

$V_{IN} = 1.5V, T_A = 25^\circ C, C_{IN} = 10\mu F, C_L = 1\mu F, R_L = 10\Omega$

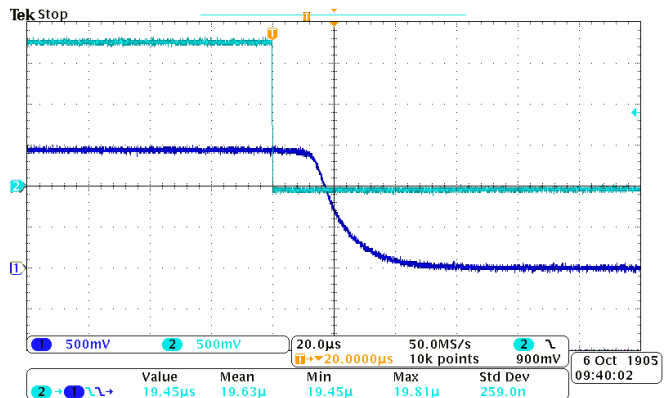


Figure 42.

TURN-Of RESPONSE TIME

$V_{IN} = 1.5V, T_A = 25^\circ C, C_{IN} = 1\mu F, C_L = 0.1\mu F, R_L = 10\Omega$

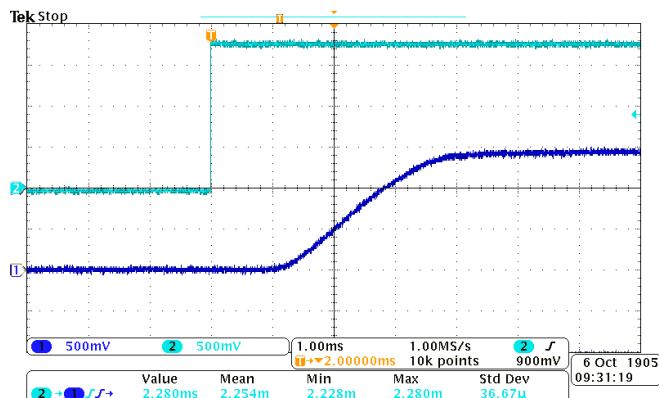


Figure 43.

TURN-Of RESPONSE TIME

$V_{IN} = 1.5V, T_A = 25^\circ C, C_{IN} = 1\mu F, C_L = 0.1\mu F, R_L = 10\Omega$

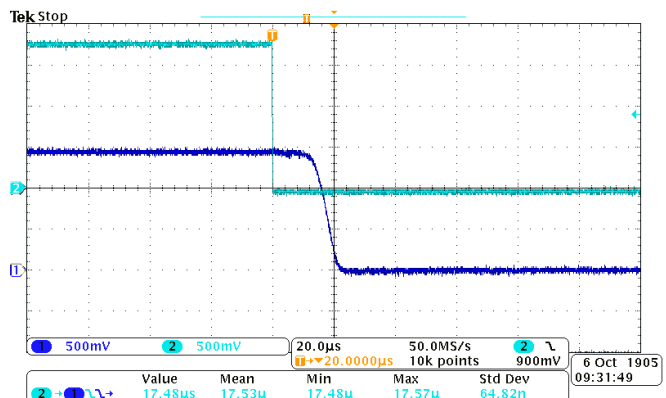


Figure 44.

APPLICATION INFORMATION

On/Off Control

The ON pin controls the state of the switch. Asserting ON high enables the switch. ON is active high and has a low threshold, making it capable of interfacing with low-voltage signals. The ON pin is compatible with standard GPIO logic threshold. It can be used with any microcontroller with 1.8-V, 2.5-V or 3.3-V GPIOs.

Input Capacitor

To limit the voltage drop on the input supply caused by transient inrush currents when the switch turns on into a discharged load capacitor or short-circuit, a capacitor needs to be placed between VIN and GND. A 1- μ F ceramic capacitor, CIN, placed close to the pins is usually sufficient. Higher values of CIN can be used to further reduce the voltage drop.

Output Capacitor

A C_{IN} to C_L ratio of 10 to 1 is recommended for minimizing V_{IN} dip caused by inrush currents during startup.

Output Pull-Down

The output pulldown is active when the user is turning off the main pass FET. The pulldown discharges the output rail to approximately 10% of the rail, and then the output pulldown is automatically disconnected to optimize the shutdown current.

Under-Voltage Lockout

The under-voltage lockout turns-off the switch if the input voltage drops below the under-voltage lockout threshold. With the ON pin active the input voltage rising above the under-voltage lockout threshold will cause a controlled turn-on of the switch which limits current over-shoots. During under-voltage lockout (UVLO), no reverse current can flow as the body diode is not engaged.

Reverse Current Protection

In a scenario where V_{OUT} is greater than V_{IN} , there could be reverse current through the body diode of the PMOS FET. The TPS22913 monitors the current through the FET and shuts off the FET when a reverse current is detected. The FET, and the output, resumes normal operation when the reverse current scenario is no longer present. When the reverse current protection (RCP) is active, no reverse current can flow as the body diode is not engaged. During under-voltage lockout (UVLO), or when the switch is disabled, no reverse current can flow as the body diode is not engaged.

Use the following formula to calculate the amount of reverse current for a particular application:

$$I_{RC} = \frac{0.044V}{R_{ON(VIN)}}$$

Where,

I_{RC} is the amount of reverse current,

$R_{ON(VIN)}$ is the on-resistance at the VIN of the reverse current condition.

Board Layout

For best performance, all traces should be as short as possible. To be most effective, the input and output capacitors should be placed close to the device to minimize the effects that parasitic trace inductances may have on normal operation. Using wide traces for V_{IN} , V_{OUT} , and GND helps minimize the parasitic electrical effects along with minimizing the case to ambient thermal impedance.

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
TPS22913BYZVR	ACTIVE	DSBGA	YZV	4	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	
TPS22913BYZVT	ACTIVE	DSBGA	YZV	4	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	
TPS22913CYZVR	ACTIVE	DSBGA	YZV	4	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	
TPS22913CYZVT	PREVIEW	DSBGA	YZV	4	250	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

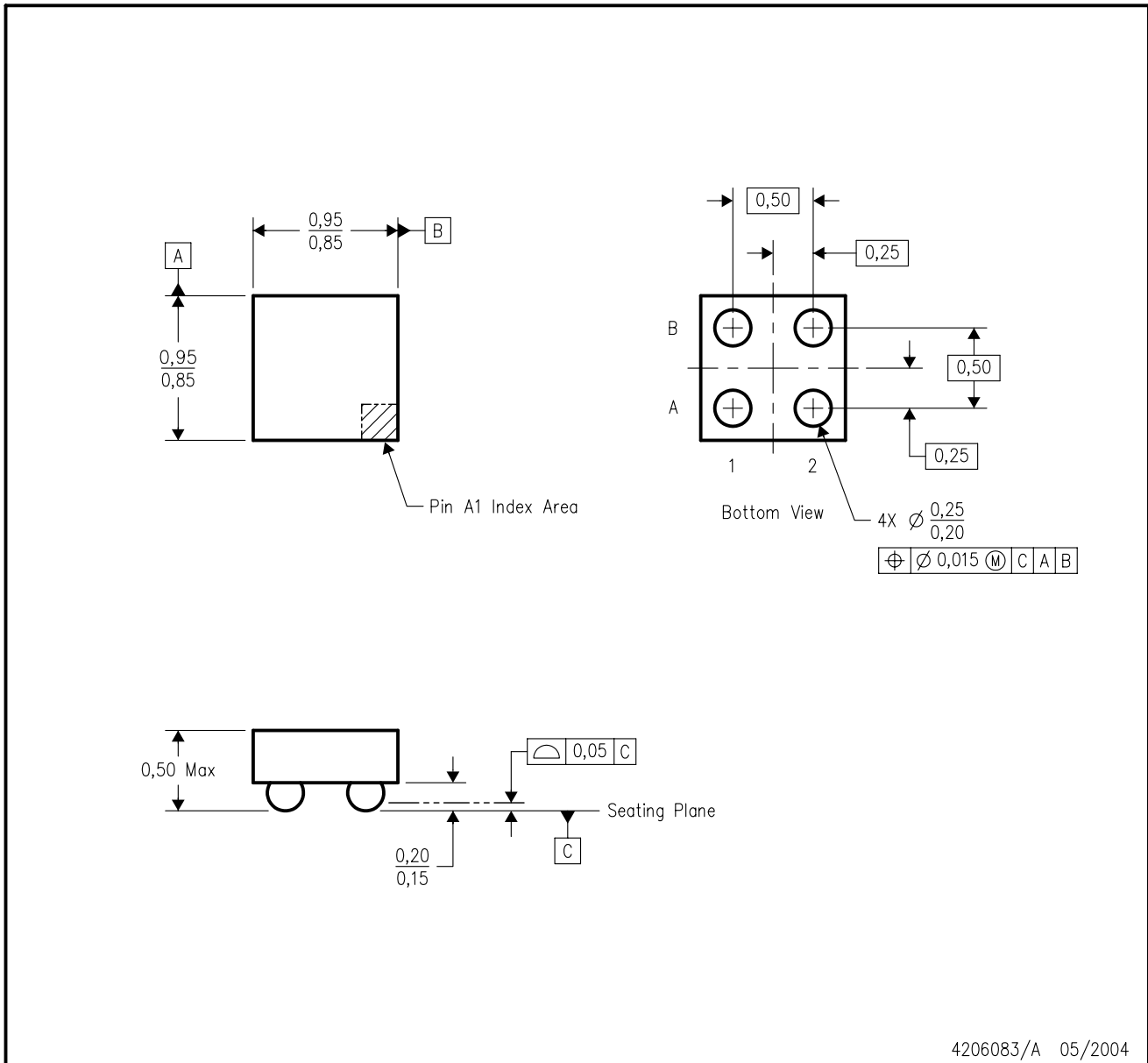
⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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YZV (S-XBGA-N4)

DIE-SIZE BALL GRID ARRAY



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. NanoFree™ package configuration.
 - D. This package contains lead-free balls. Refer to the 4 YEV package (drawing 4206082) for tin-lead (SnPb) balls.

NanoFree is a trademark of Texas Instruments.

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